

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A light emitting device, comprising:
  - a first conductive semiconductor layer;
  - an active layer formed on the first conductive semiconductor layer;
  - a second conductive semiconductor layer formed on the active layer;
  - a high concentration GaN-based semiconductor layer formed on the second conductive semiconductor layer;
  - a first metal-Ga compound layer formed on the high concentration GaN-based semiconductor layer;
  - a first metal layer formed on the first metal-Ga compound layer, the first metal layer being a substantially pure metal layer;
  - a third metal-Al compound layer formed on the first metal layer; and
  - a conductive oxidation preventive layer formed on the third metal-Al compound layer.
- 2-3. (Cancelled)
4. (Previously Presented) The light emitting device according to claim 1, wherein the second conductive semiconductor layer is a P-type or N-type GaN-based layer.
5. (Previously Presented) The light emitting device according to claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W.
6. (Cancelled)

7. (Previously Presented) The light emitting device according to claim 1, wherein the third metal is of one selected from the group consisting of Ni, Pt and Pd.

8. (Previously Presented) The light emitting device according to claim 1, wherein the third metal is of a metal or compound having a high reactivity with Al.

9. (Cancelled)

10. (Previously Presented) The light emitting device according to claim 1, wherein the conductive oxidation preventive layer is of Au, or is of a multi-metal or compound of two or more kinds containing Au.

11-52. (Cancelled)

53. (Previously Presented) The light emitting device according to claim 1, wherein the first conductive semiconductor layer is an N-type layer, and the second conductive semiconductor layer and the high concentration GaN-based semiconductor layer are P-type layers.

54. (Previously Presented) The light emitting device according to claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.

55. (Previously Presented) The light emitting device according to claim 1, comprising a transparent electrode layer formed between the high concentration GaN-based semiconductor layer and the first metal-Ga compound layer.

56. (Previously Presented) The light emitting device according to claim 55, wherein the high concentration GaN-based layer is a P-type or N-type layer.

57. (Previously Presented) The light emitting device according to claim 55, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.

58. (Previously Presented) The light emitting device according to claim 1, wherein the first metal-Ga compound layer, the first metal layer, the third metal-Al compound layer, and the conductive oxidation preventive layer form an electrode.

59. (Previously Presented) The light emitting device according to claim 1, wherein the first conductive semiconductor layer comprises at least one of an Al material or an In material.

60. (Previously Presented) The light emitting device according to claim 57, wherein the conductive oxidation preventive layer comprises one of Au, a multi-metal, and a compound of two or more kinds containing Au.

61. (Previously Presented) The light emitting device according to claim 53, wherein the second conductive semiconductor layer comprises a vacancy structure.

62. (Previously Presented) The light emitting device according to claim 1, wherein the third metal-Al compound layer is a metal layer.

63. (Previously Presented) The light emitting device according to claim 1, wherein a high concentration GaN-based semiconductor layer comprises a carrier concentration of more than  $10^{18} \text{ cm}^{-3}$ .

64. (Previously Presented) The light emitting device according to claim 1, wherein a high concentration GaN-based semiconductor layer comprises a carrier concentration more than a carrier concentration of the second type conductive semiconductor layer.